Elektronische Bauelemente

# PZT195

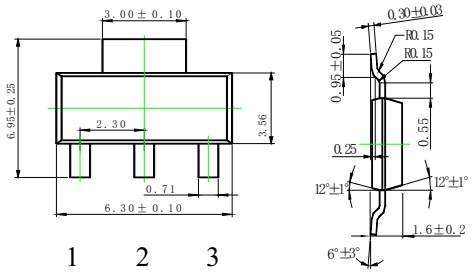
## PNP Silicon Planar Medium Power Transistor

RoHS Compliant Product

## Features

* -60 Voltage $V_{CEO}$.
* 1 Amps continuous current.
* Complementary to PZT194

**SOT-223**



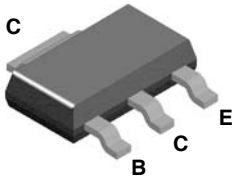

1. BASE
2. COLLECTOR
3. EMITTER

## Mechanical Data

**Case:** SOT-223 Plastic Package

**Weight:** approx. 0.021g

**Marking Code:** 195




## Maximum Ratings and Thermal Characteristics

($T_A$ = 25°C unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Junction Temperature | Tj | +150 | °C |
| Storage Temperature | Tstg | -55 to +150 | °C |
| Collector-Base Voltage | $V_{CBO}$ | -80 | V |
| Collector-Emitter Voltage | $V_{CEO}$ | -60 | V |
| Emitter-Base Voltage | $V_{EBO}$ | -5 | V |
| Collector Current (DC) | $I_C$ | -1 | A |
| Collector Current (Pulse) | $I_C$ | -0.2 | A |
| Total Power Dissipation | $P_D$ | 2.0 | W |

**Notes:** Device on alumina substrate.

## Electrical Characteristics ($T_J$ = 25°C unless otherwise noted)

| Parameter | Symbol | Min | Typ. | Max | Unit | Test Conditions |
|---|---|---|---|---|---|---|
| Collector-Base Breakdown Voltage | $BV_{CBO}$ | -80 | - | - | V | $I_C$=-100uA, $I_E$=0 |
| Collector-Emitter Breakdown Voltage | *$BV_{CEO}$ | -60 | - | - | V | $I_C$=-10mA, $I_B$=0 |
| Emitter-Base Breakdown Voltage | $BV_{EBO}$ | -5 | - | - | V | $I_E$=-100uA, $I_C$=0 |
| Collector-Emmiter Breakdown Voltage | $I_{CBO}$ | - | - | -100 | nA | VCB=-60V, IE=0 |
| Collector-Base Cutoff Current | $I_{CES}$ | - | - | -100 | nA | VCES=-60V |
| Emitter-Base Cutoff Current | $I_{EBO}$ | - | - | -100 | nA | VEB=-4V, IC=0 |
| Collector Saturation Voltage 1 | *$V_{CE(sat)}$1 | - | - | -0.3 | V | IC=-500mA, IB=-50mA |
| Collector Saturation Voltage 2 | *$V_{CE(sat)}$2 | - | - | -0.6 | V | IC=-1A, IB=-100mA |
| Base Saturation Voltage | *$V_{BE(sat)}$ | - | - | -1.2 | V | IC=-1A, IB=-100mA |
| Base-Emitter Voltage | *$V_{BE(on)}$ | - | - | -1.0 | V | VCE=-5V, IC=-1A |
| DC Current Gain 1 | *$h_{FE}$1 | 100 | - | - | - | VCE=-5V, IC=1mA |
| DC Current Gain 2 | *$h_{FE}$2 | 100 | - | 300 | - | VCE=-5V, IC=-500mA |
| DC Current Gain 3 | *$h_{FE}$3 | 80 | - | - | - | VCE=-5V, IC=-1A |
| DC Current Gain 4 | *$h_{FE}$4 | 15 | - | - | - | VCE=-5V, IC=-2A |
| Gain-Bandwidth Product | fT | 150 | - | - | MHz | VCE=-10V, IC=-50mA, f=100MHz |
| Output Capacitance | Cob | - | - | 10 | pF | VCB=-10V, IE=0, f=1MHz |

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## Medium Power Transistor

### Characteristics Curve

